

15 **IN THE CLAIMS:**

1. (Currently Amended) A semiconductor light emitting device, comprising:

a semiconductor multilayer structure composed of a p-semiconductor layer, a quantum well emission layer, and an n-semiconductor layer each made of a nitride semiconductor and laminated in the stated order, light from the emission layer exiting through
20 the n-semiconductor layer; and

a p-electrode facing and in electrical connection with the p-semiconductor layer, wherein

the p-semiconductor layer has, on a surface facing toward the p-electrode, (i) high-defect of dislocation-density regions in which defects of dislocation are localized and (ii)
25 low-defect of dislocation-density regions, the high- and low-defect of dislocation-density regions being at regularly or selectively distributed locations,

the p-electrode has, on a surface facing toward the p-semiconductor layer, a plurality of projections or depressions that are distributed substantially uniformly, and

the p-electrode is directly in contact, at a top surface thereof, with the low-defect
30 of dislocation-density regions of the p-semiconductor layer.

2.-3. (Cancelled)

4. (Previously Presented) The semiconductor light emitting device according to Claim 1, wherein

the p-electrode is made of a metal that reflects light from the emission layer toward the n-semiconductor layer.

5. (Original) The semiconductor light emitting device according to Claim 4, further comprising

an insulator disposed on a recessed surface of the p-electrode to fill a space between the recessed surface and the p-semiconductor layer.

6. (Original) The semiconductor light emitting device according to Claim 5, wherein

the insulator is made of a material transparent to light emitted by the emission layer.

7. (Original) The semiconductor light emitting device according to Claim 5, wherein

the insulator has a substantially same refractive index as a refractive index of the nitride semiconductor forming the p-semiconductor layer.

8. (Previously Presented) The semiconductor light emitting device according to Claim 1, wherein

a drive current for driving the semiconductor light emitting device is maintained within such a range that results in an average current density not exceeding 50 A/cm^2 , the
5 average current density being calculated by dividing the drive current by an area of a main surface of the emission layer,

the p-electrode faces substantially entirely of the main surface of the emission layer, and

a ratio between the top and recessed surfaces of the p-electrode is determined so
10 that an electric current flowing through the top surface of the p-electrode measures at least 100
A/cm² in current density.

9. (Currently Amended) The semiconductor light emitting device according to
Claim 1, wherein

the high-defect of dislocation-density regions are distributed to define one of a
quadrangular grid, a hexagonal grid, a triangular grid, and a staggered grid.

10. (Previously Presented) The semiconductor light emitting device according to
Claim 1, wherein

an intensive-injection region is realized by a contact structure of the p-
semiconductor layer with the p-electrode.

11. (Original) The semiconductor light emitting device according to Claim 10,
wherein

the semiconductor multilayer structure has, on a surface facing toward the p-
electrode, a plurality of projections or depressions that are distributed substantially uniformly,

5 and

the semiconductor multilayer structure is in contact with the p-electrode at a top
surface of the p-semiconductor layer.

12. (Original) The semiconductor light emitting device according to Claim 11,
wherein

the p-electrode is made of a metal that reflects light from the emission layer toward the n-semiconductor layer.

13. (Original) The semiconductor light emitting device according to Claim 11, wherein

a recessed surface of the semiconductor multilayer structure is present in the n-semiconductor layer.

14. (Currently Amended) The semiconductor light emitting device according to Claim 11, wherein

the semiconductor multilayer structure has, on the surface facing toward the p-electrode, a high-defect of dislocation region in which lattice defects of dislocation are localized
5 and a low-defect of dislocation region formed adjacent to the high-defect of dislocation region, and

the low-defect of dislocation region is present at the top surface of the semiconductor multilayer structure.

15. (Original) The semiconductor light emitting device according to Claim 1, further comprising:

a base substrate supporting the semiconductor multilayer structure from a direction of the p-semiconductor layer; and

5 a phosphor film disposed on a main surface of the semiconductor multilayer structure facing away from the base substrate, the phosphor film extending across a side surface of the semiconductor multilayer structure to the base substrate.

16. (Previously Presented) A lighting module comprising:

a mounting substrate; and

the semiconductor light emitting device as defined in Claim 1.

17. (Original) A lighting device comprising, as a light source, the lighting module as defined in Claim 16.

18. (Previously Presented) A surface mounting device comprising:

a substrate;

a semiconductor light emitting device as defined in Claim 1, and mounted on the substrate; and

5 a resin molding the semiconductor device.

19. (Previously Presented) A dot-matrix display device comprising:

semiconductor light emitting devices as defined in Claim 1 and are arranged in a matrix.